

ABSTRACT OF THE DISCLOSURE

A photoresist layer is exposed two or more times. At least one exposure is conducted through a regular mask, and at least one exposure through a modified mask with a clear region overlapping the position of a non-clear region of the first mask. The
5 radiation dose used with the modified mask is insufficient by itself to create a resist pattern on the substrate. The exposure through the modified mask alleviates the resist underexposure in concave corners of the opaque pattern of the regular mask. Instead of the modified mask, an exposure without a mask can be performed.

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